

Brief Description of the Drawings

FIGs. 1(a), 1(b) and 1(c) show exemplary semiconductor structures according to varying embodiments of the invention;

FIGs. 2(a), 2(b), 2(c), 2(d), ~~and 2(e)~~ ^{2(f) and 2(g)} show an exemplary semiconductor structure according to an embodiment of the invention;

FIGs. 3(a), 3(b), 3(c), 3(d) and 3(e) show a process to form buried conductors according to an embodiment of the invention; and,

FIG. 4 shows a representative semiconductor memory device in conjunction with which embodiments of the invention may be practiced.

Detailed Description of the Invention

In the following detailed description of exemplary embodiments of the invention, reference is made to the accompanying drawings which form a part hereof, and in which is shown by way of illustration specific exemplary embodiments in which the invention may be practiced. These embodiments are described in sufficient detail to enable those skilled in the art to practice the invention, and it is to be understood that other embodiments may be utilized and that logical, mechanical, electrical and other changes may be made without departing from the spirit or scope of the present invention. The following detailed description is, therefore, not to be taken in a limiting sense, and the scope of the present invention is defined only by the appended claims.

The detailed description is divided into five sections. In the first section, exemplary structures having buried conductors are described. In the second section, a method by which buried conductors may be formed according to one embodiment of the invention is provided. In the third section, processes to form the exemplary structures of the first section are given. In the fourth section, a representative memory device in conjunction with which embodiments of the invention may be practiced is presented. Finally, in the fifth section, a conclusion is provided.